

a gate electrode stack disposed on the gate dielectric film, wherein the stack includes a plurality of layers located over the gate dielectric film and forms continuously vertical sidewalls; and

a plurality of composite spacers each extending continuously from a bottom to a top of said continuously vertical sidewalls,

wherein

each of said composite spacers further comprises a nitride spacer vertically stacked above an oxide spacer,

said oxide spacer extending along the bottom of said continuously vertical sidewalls to an intermediate point in between the top and the bottom of said continuously vertical sidewalls, and

said nitride space spacer extending from the intermediate point to the top of said continuously vertical sidewalls.